

AMENDMENTS TO THE CLAIMS:

Please amend claims by canceling claims 2-23 as indicated on the following listing of all the claims in the present application after this Amendment:

1. (original) A non-volatile memory formed on a substrate, comprising:
an array of non-volatile memory cells including a plurality of rows of cells extending in a first direction across the substrate and being separated in a second direction by spaces therebetween, the first and second directions being orthogonal with each other, the cells individually including source/drain regions on opposite sides of at least one electron storage element in said first direction that are shared with adjacent cells of the same row,
strips of dielectric material elongated in the first direction and extending into the substrate in the spaces between the rows of cells in order to provide electrical isolation between the memory cells of adjacent rows including isolation of their source/drain regions in said second direction,
first electrically conductive strips elongated in the second direction and spaced apart in the first direction coincident with a plurality of adjacent source/drain diffusions, the first conductive strips individually extending across and contacting source/drain regions of a plurality of adjacent rows of cells and the dielectric material strips therebetween, and
second electrically conductive strips positioned above the substrate and individually including gates therealong that are elements of adjacent memory cells.

2.-23. (Canceled)